International Application No. PCT/DE2003/002553
Attorney Docket No. 056226.56006US
Preliminary Amendment dated March 18, 2005

## AMENDMENTS TO THE ABSTRACT:

Please substitute the new Abstract of the Disclosure submitted herewith on a separate page for the original Abstract presently in the application.

The invention relates to an An arrangement for a junction between a microstripline and waveguide comprising is provided. The arrangement includes [[-]] a microstripline (ML) which is fitted on the upper face of a dielectric substrate (S), [[-]] a waveguide which is fitted on the upper face of the substrate (S) and has an opening (OB) on at least one end surface and has a structure (ST) which is in the form of a step or steps in the area of the opening (OB) on one side wall and is conductively connected in at least one part (ST1) to a microstripline (ML), and wherein one. One side wall of the waveguide is a metallized layer (LS) formed on the substrate [[(S), - a]]. A cutout (A) which is formed in the metallized layer (LS) and into which the microstripline (ML) projects[[,]]. [[-]] A rear-face metallization (RM) which is formed on the rear face of the substrate (S), and [[-]] electrically conductive via holes (VM) between the metallized layer (LS) on the upper face of the substrate (S) and the rear-face metallization (RM), which surround the cutout (A).

(Figure 4)

## **ABSTRACT**

An arrangement for a junction between a microstripline and a waveguide is provided. The arrangement includes a microstripline fitted on the upper face of a dielectric substrate, a waveguide fitted on the upper face of the substrate and has an opening on at least one end surface and has a structure which is in the form of a step or steps in the area of the opening on one side wall and is conductively connected in at least one part to a microstripline. One side wall of the waveguide is a metallized layer formed on the substrate. A cutout is formed in the metallized layer and into which the microstripline projects. A rear-face metallization is formed on the rear face of the substrate, and electrically conductive via holes between the metallized layer on the upper face of the substrate and the rear-face metallization, which surround the cutout.